

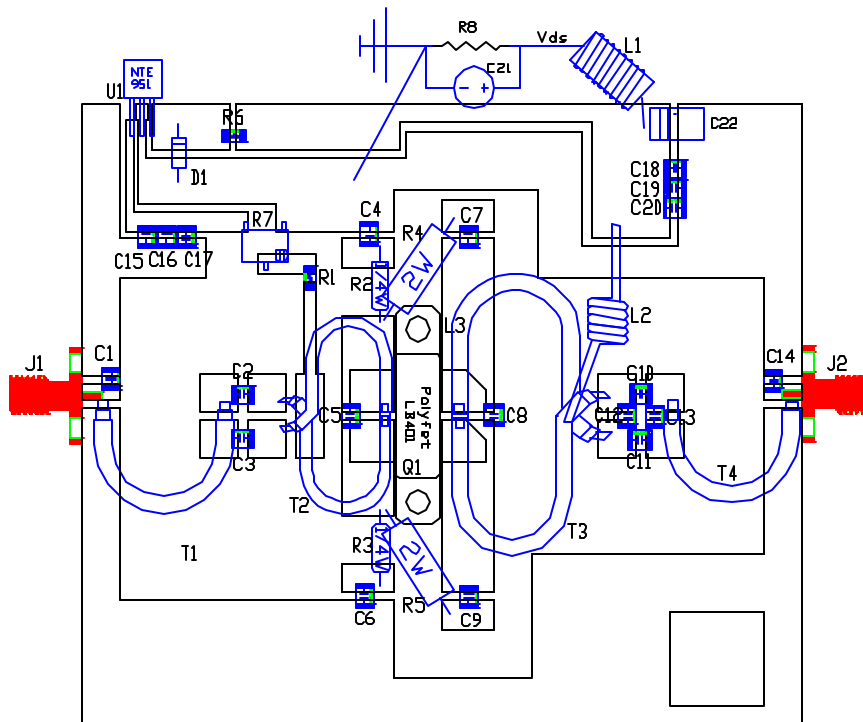
515C
CST M

1000

PERCUTIP
10001
TYPE F

1000

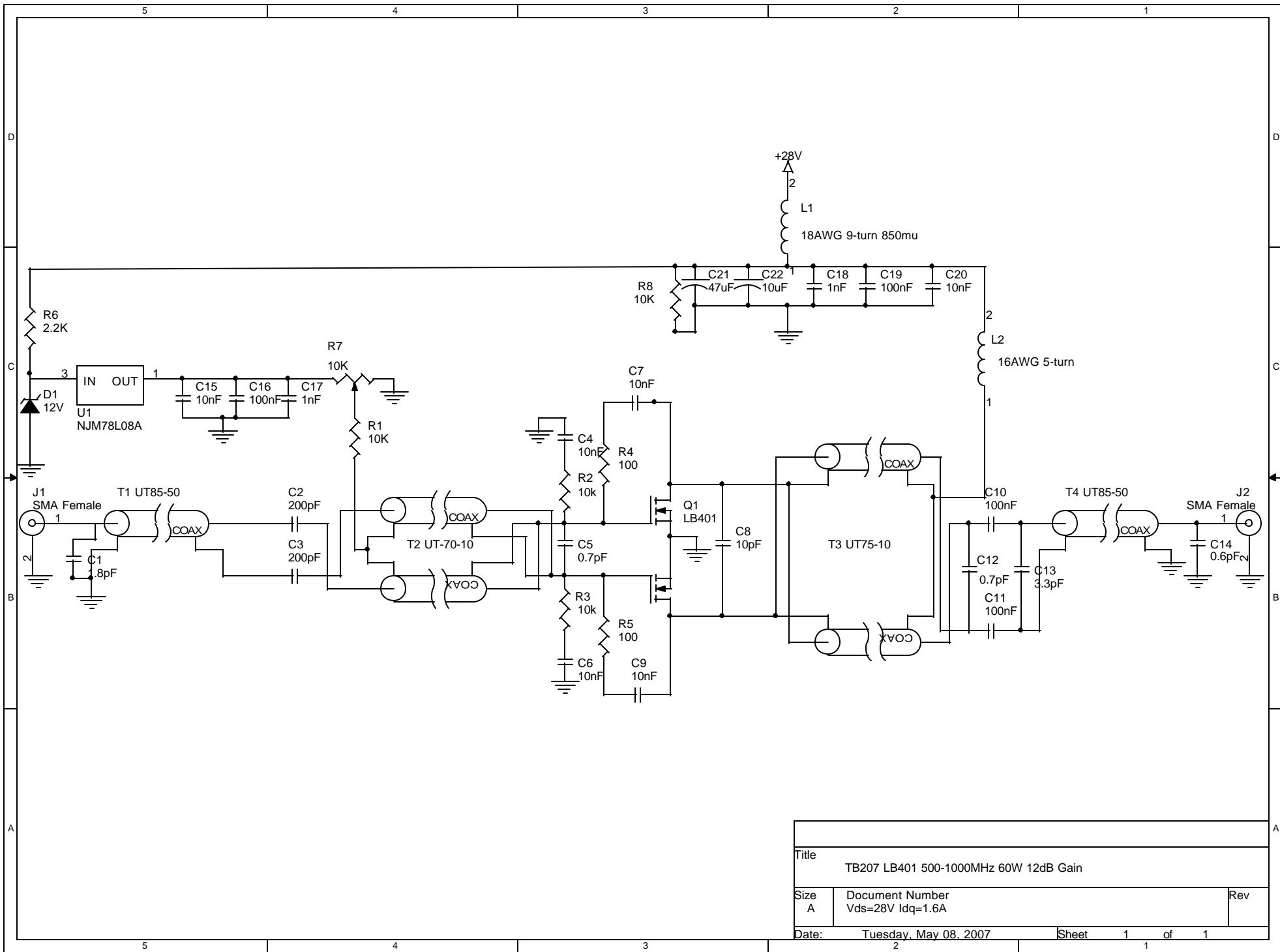




SYMBOL	VALUE	DESCRIPTION
C1	1.8pF	ATC-100B Chip Cap
C2, C3	200pF	ATC-200B Chip Cap
C4,C6,C7,C9,C15,C20	10nF	ATC-200B Chip Cap
C5,C12	0.7pF	ATC-100B Chip Cap
C8	10pF	ATC-100B Chip Cap
C13	3.3pF	ATC-100B Chip Cap
C14	0.6pF	ATC-100B Chip Cap
C10,C11,C16,C19	100nF	ATC-200B Chip Cap
C17,C18	1nF	ATC-200B Chip Cap
C21	47uF	Aluminum Electrolytic
C22	10uF	Vishay/Sprague Tantalum
D1	12V	Axial Zener Diode
J1, J2	---	SMA Female
L2	16AWG5-turn, ID: 0.2"	
Q1	LB401	Polyfet Transistor
R4, R5	100 Ohm	2-Watt Axial
R2, R3, R8	10K Ohm	1/4-Watt Axial
R6	22K Ohm	1206 Chip Resistor
R1	10K	1206 Chip Resistor
R7	10K	6mm, multi-turn POT
T1 & T4	1.5"	UTB5-50
T2	1.5"	UT70-10
T3	1.75"	UT75-10
U1	---	NJM78L08A
Vdd	28V	Drain Voltage
Bias	1.6A	Quiescent Drain Current

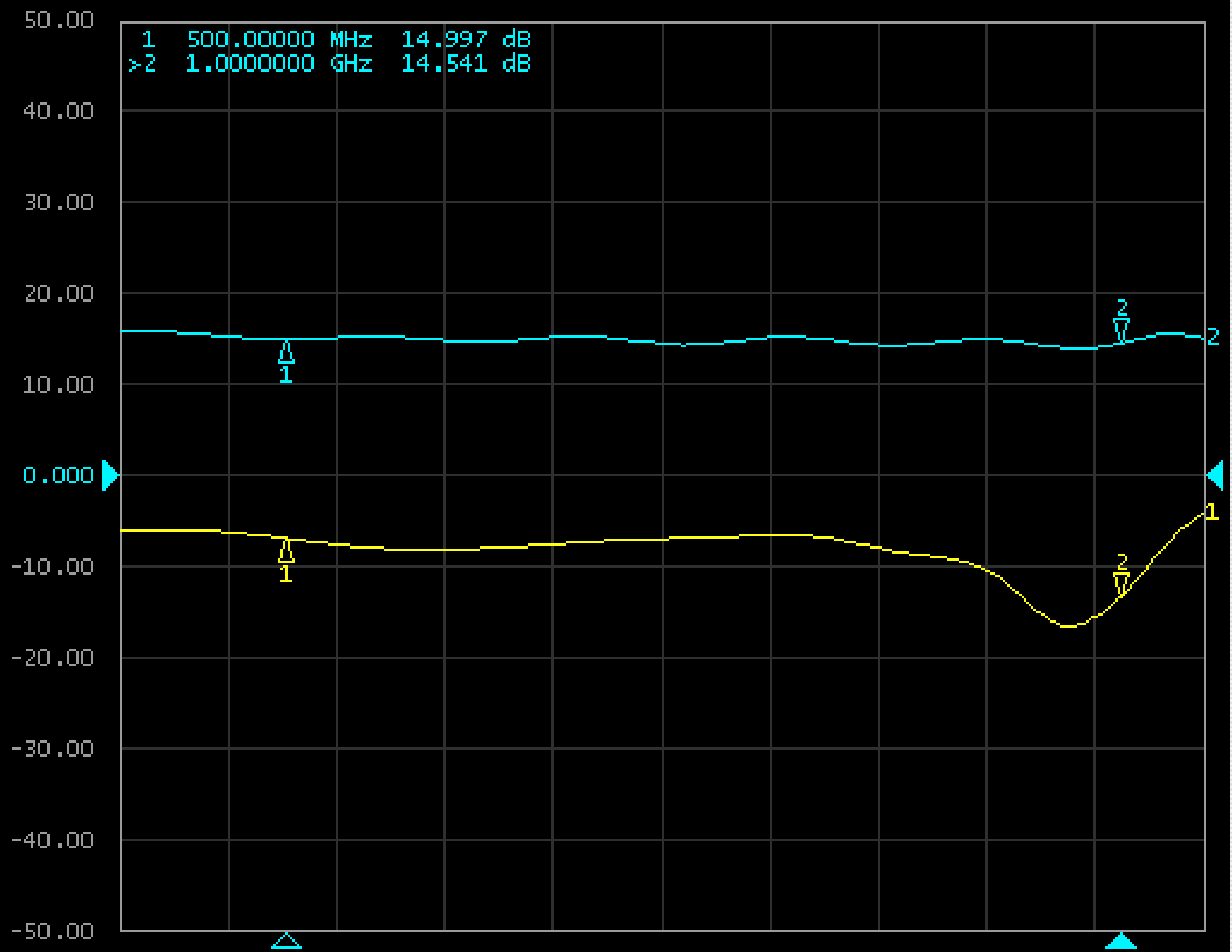
PCB Material : Double-side Teflon ER=2.5, H=0.064in, 2oz

DRN BY: M. Cervantes	05/07/2007	POLYFET RF DEVICES
CHKD :		
ELECT : M. Cervantes	05/07/2007	TB207 LB401 500-1000MHz 60W 12dB
MECH : T. Chang	04/01/2005	
PROC :		SIZE FSCM NO
QUAL :		Vdd=28V Idq=1.6A
PGNS :		REV B
		SCALE : 1 : 1
		SHEET 1 OF 1

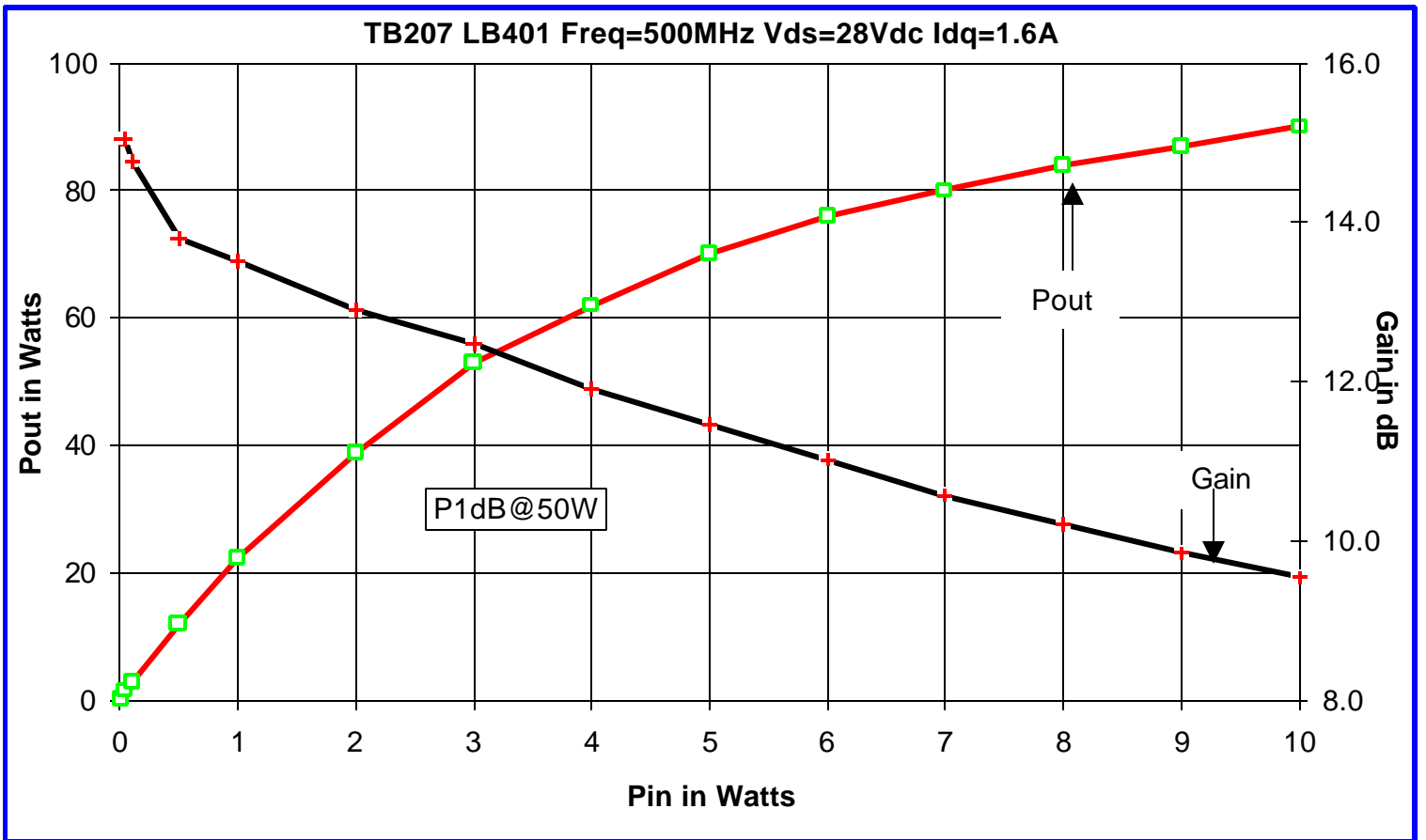
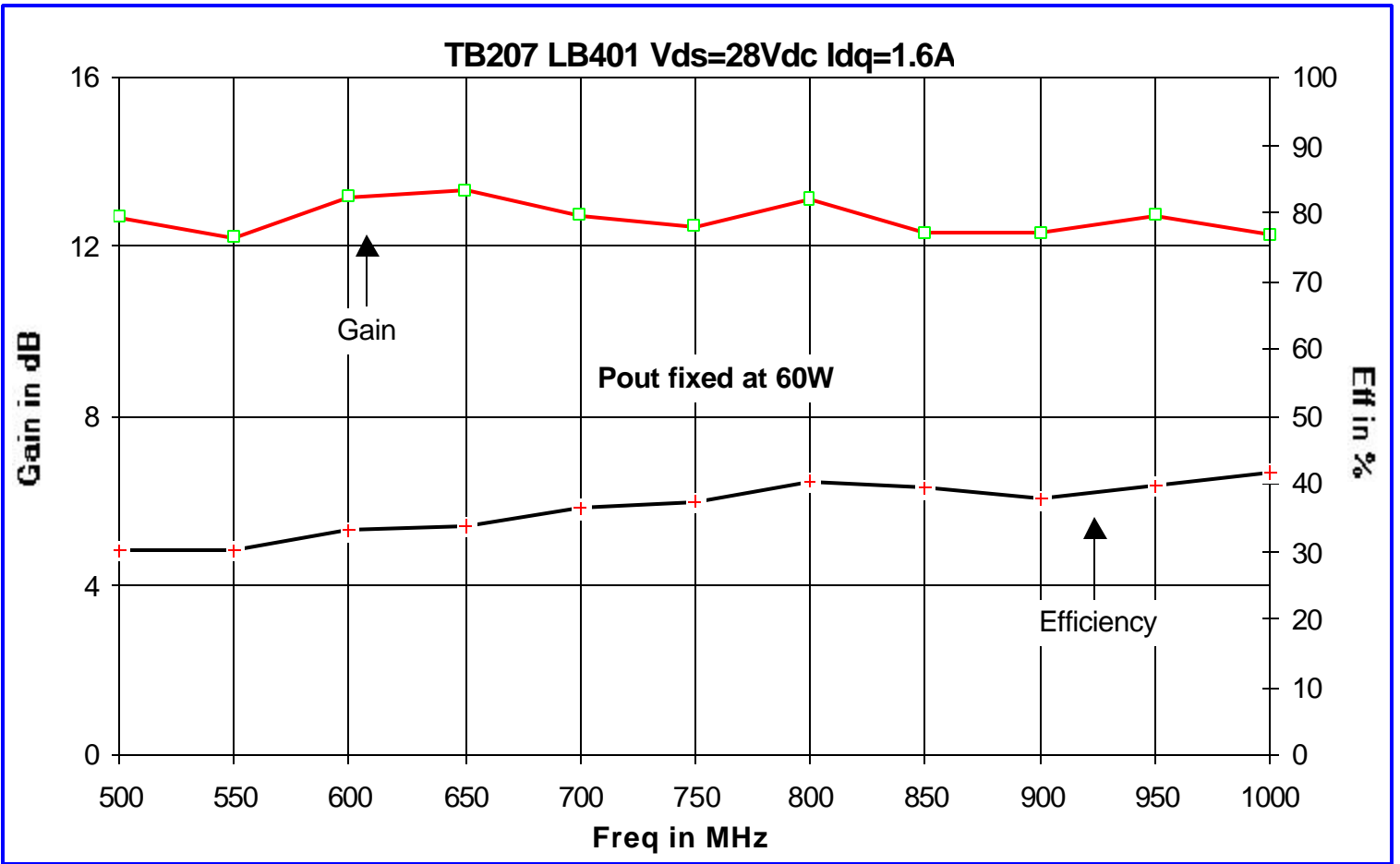


Title		
TB207 LB401 500-1000MHz 60W 12dB Gain		
Size	Document Number	Rev
A	Vds=28V Idq=1.6A	
Date:	Tuesday, May 08, 2007	Sheet 1 of 1

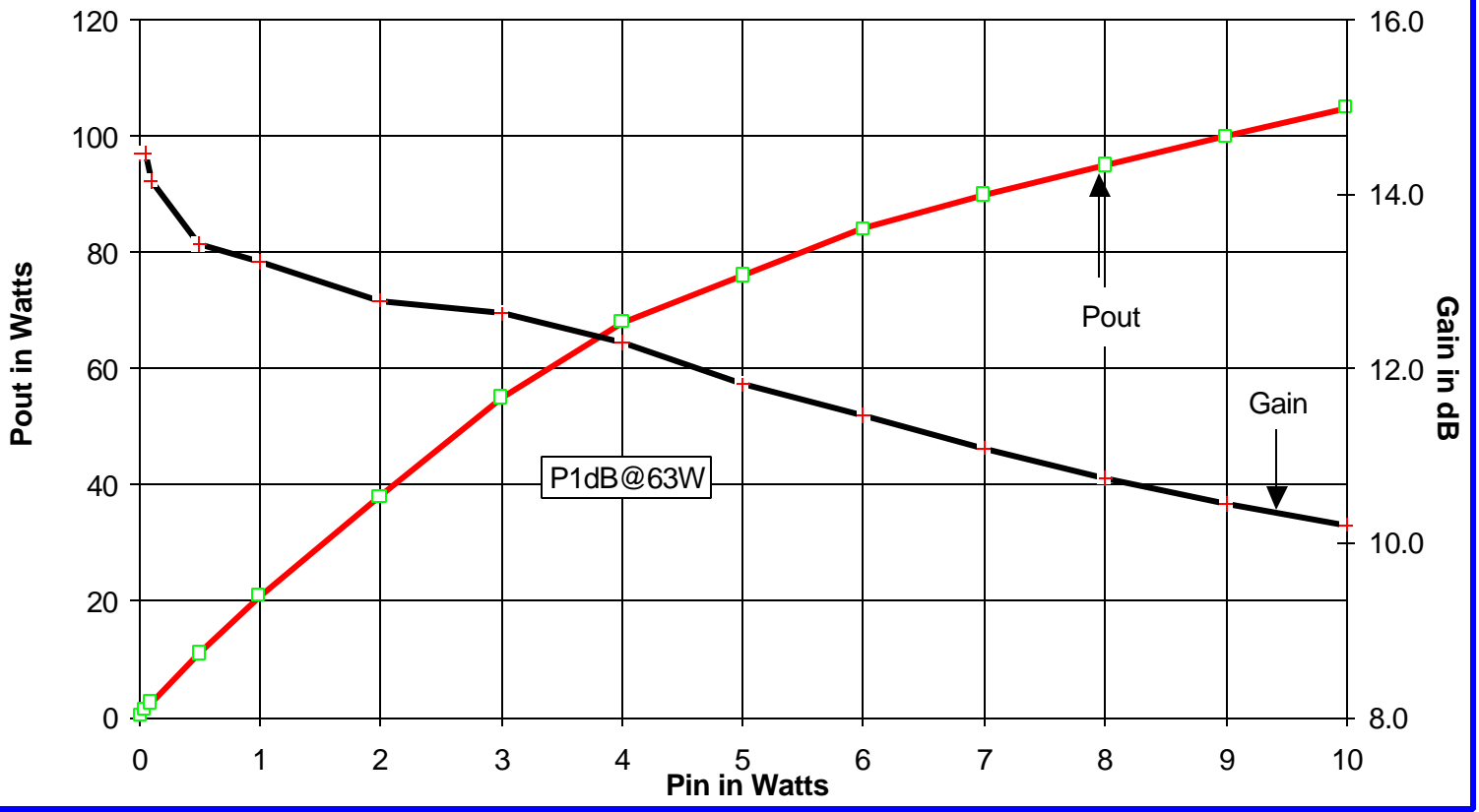
Tr1 S11 Log Mag 10.00dB/ Ref 0.000dB [F1]
Tr2 S21 Log Mag 10.00dB/ Ref 0.000dB [ER]



1 Start 400 MHz IFBW 30 kHz Stop 1.05 GHz C?



TB207 LB401 Freq=750MHz Vds=28Vdc Idq=1.6A



TB207 LB401 Freq=1000MHz Vds=28Vdc Idq=1.6A

